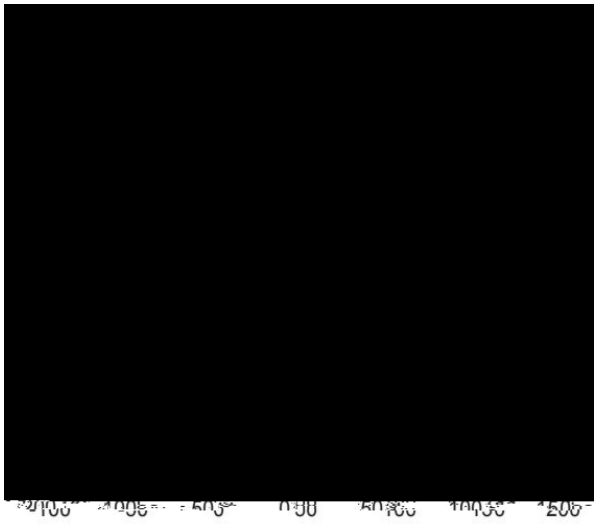
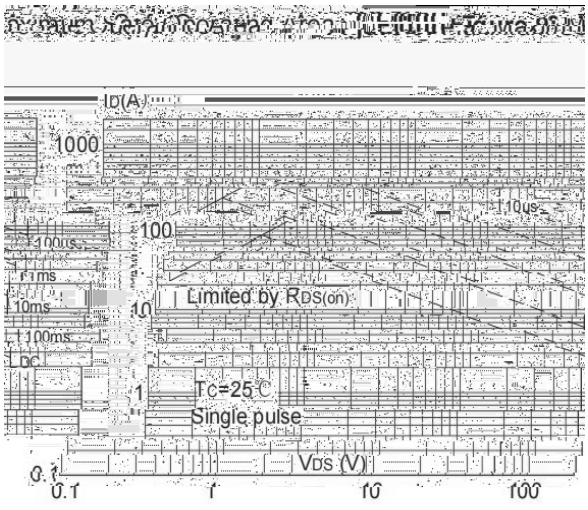
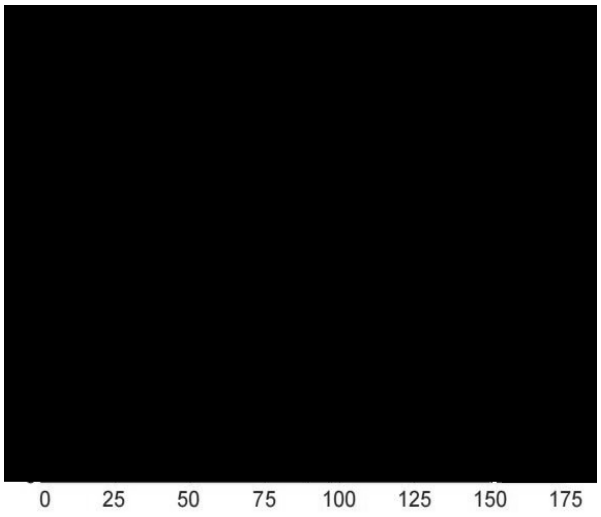
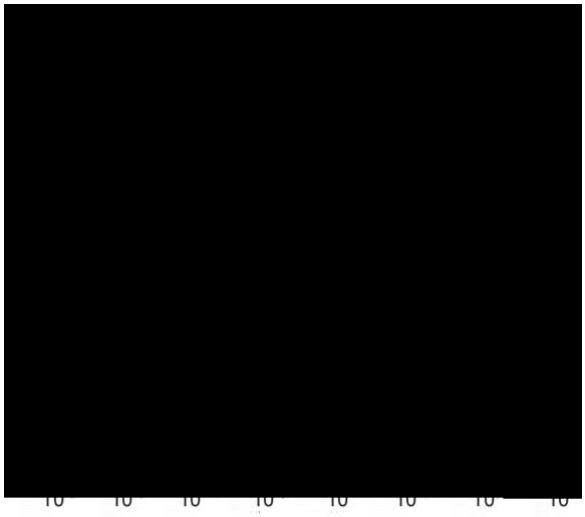
Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	60	-	-
Zero Gate Voltage Drain Current	V_{DS} =60 V, V_{GS} = 0 V	-	-	1
Gate Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100
Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250μA	2	-	4
Drain-Source on-Resistance	V_{GS}=10V, I_D=30A	-	5.3	6.9
Forward Transconductance	V_{DS} = 5 V, I_D = 10 A	10	-	-
Input Capacitance	V_{DS}=30V, V_{GS}=0			






ID(A)
1000
100
10
1
0.1
10us
100ms
1ms
10ms
100ms
DC
Limited by RDS(on)
TC=25℃
Single pulse
VDS (V)
0.1
1
10
100


0
25
50
75
100
125
150
175



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